

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	110mΩ@-4.5V	-1.2A
	140mΩ@-2.5V	

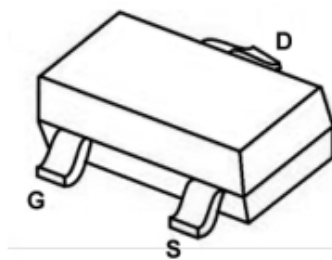
Feature

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$ and Low Gate Charge

Applications

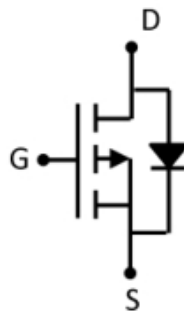
- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

Package

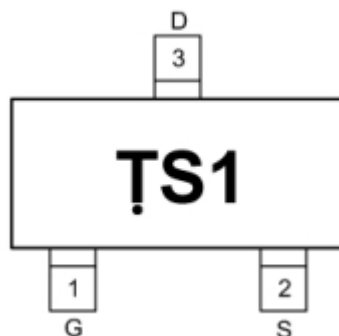


SOT-323

Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-1.2	A
Pulsed Drain Current	I_{DM}	-2.8	A
Power Dissipation	P_D	0.29	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	431	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

Electrical characteristics

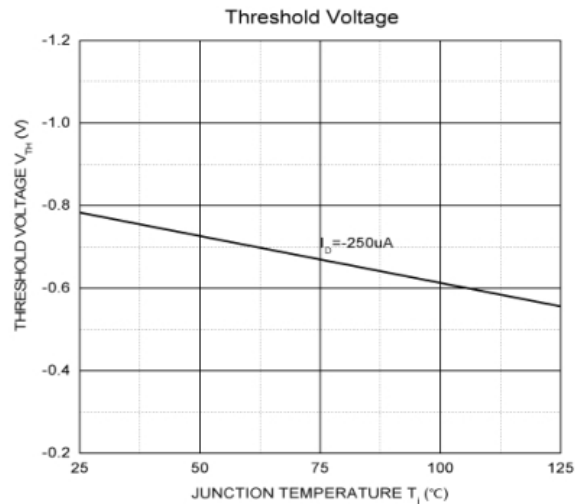
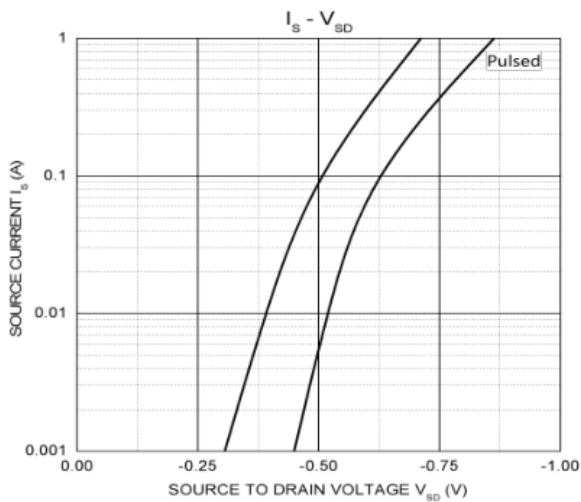
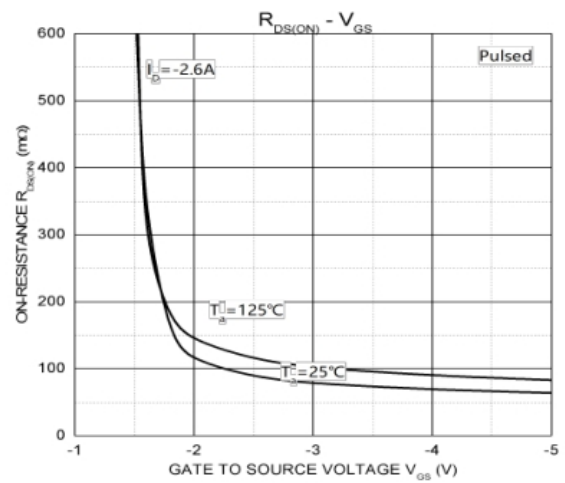
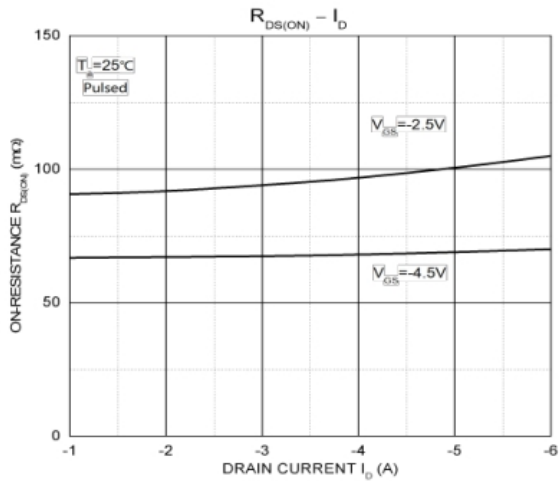
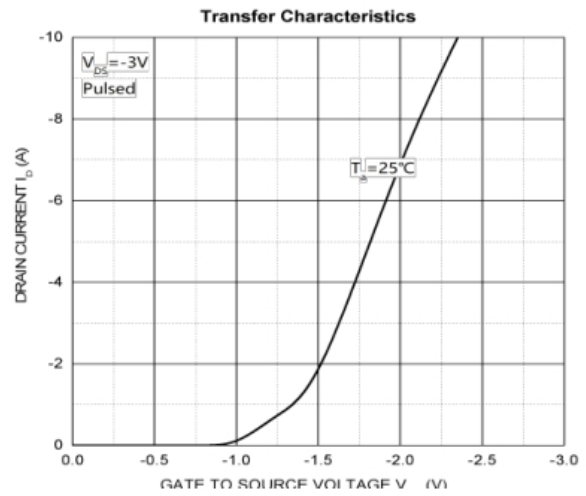
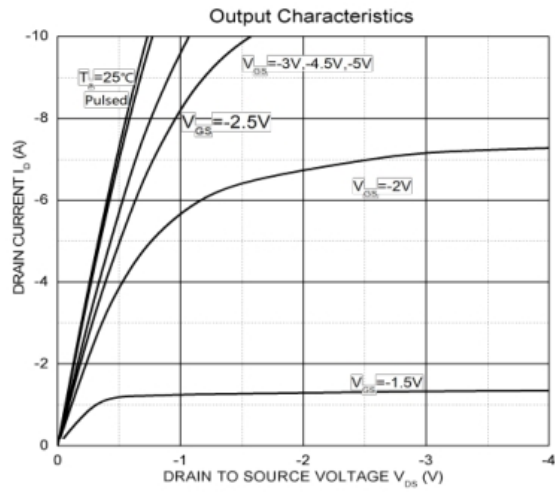
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	uA
Gate-body leakage current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V			±100	uA
Gate threshold voltage ⁽¹⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250μA	-0.5	-0.7	-1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -0.5A		110	140	mΩ
		V _{GS} = -2.5V, I _D = -0.5A		140	180	
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{DS} = -8V, V _{GS} =0V, f=1MHz		640		pF
Output capacitance	C _{oss}			120		
Reverse transfer capacitance	C _{rss}			82		
Switching Characterisitics						
Total Gate Charge	Q _g	V _{DS} = -10V,V _{GS} = -4.5V, I _D = -3A		5.5		nC
		V _{DS} = -10V,V _{GS} = -2.5V, I _D = -3A		3.3		
Gate-Source Charge	Q _{gs}			0.7		
Gate-Drain Charge	Q _{gd}			1.3		
Turn-on Delay Time	T _{d(on)}	V _{GS} = -4.5V, V _{DD} = -4V, I _D = -1A, R _{GEN} =6.2Ω		6.2		nS
Turn-on Rise Time	T _r			15		
Turn-Off Delay Time	T _{d(off)}			26		
Turn-Off Fall Time	t _f			18		
Source-Drain Diode Characteristics						
Diode Forward voltage	V _{DS}	I _S = -1A, V _{GS} = 0V			-1.2	V

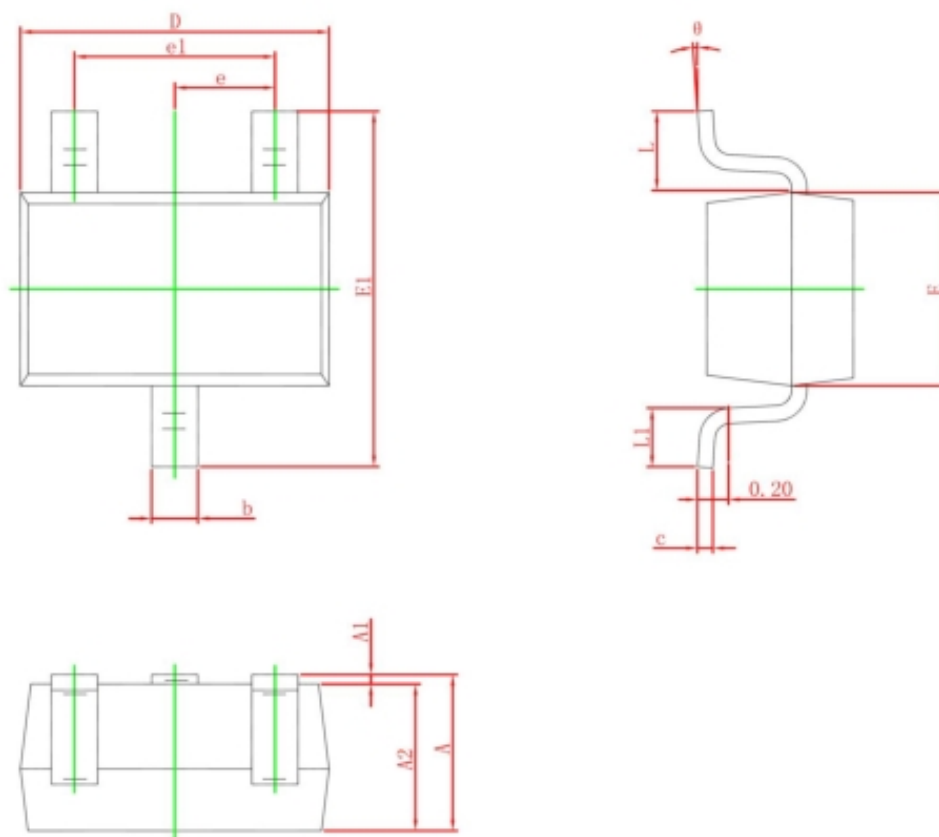
Notes:

1. Pulse Test: Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

Typical Characteristics



SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.000	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°